



## 16N50

Preliminary

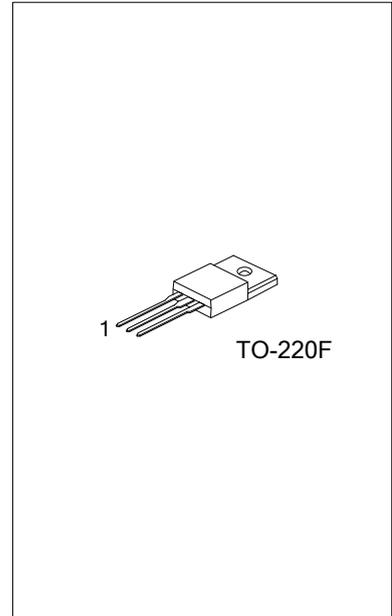
Power MOSFET

### 16 Amps, 500 Volts N-CHANNEL POWER MOSFET

#### DESCRIPTION

The UTC **16N50** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

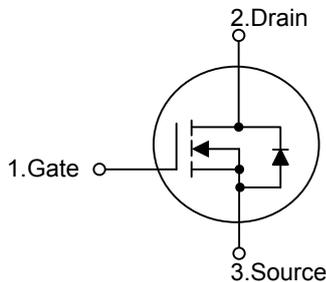
The UTC **16N50** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.



#### FEATURES

- \* 16A, 500V,  $R_{DS(ON)}=0.38\Omega @ V_{GS}=10V$
- \* High Switching Speed
- \* 100% Avalanche Tested

#### SYMBOL



#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
16N50L-TF3-T	16N50G-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

16N50L-TF3-T	(1)Packing Type	(1) T: Tube
	(2)Package Type	(2) TF3: TO-220
	(3)Lead Free	(3) G: Halogen Free, L: Lead Free

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■ ABSOLUTE MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DSS}$	500	V
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Drain Current	Continuous ( $T_C=25^\circ\text{C}$ )	$I_D$	16 (Note 2)
	Pulsed (Note 3)	$I_{DM}$	64 (Note 2)
Avalanche Current (Note 3)	$I_{AR}$	16	A
Avalanche Energy	Single Pulsed (Note 4)	$E_{AS}$	780
	Repetitive (Note 5)	$E_{AR}$	20
Peak Diode Recovery $dv/dt$ (Note 5)	$dv/dt$	4.5	V/ns
Power Dissipation	$T_C=25^\circ\text{C}$	$P_D$	52
	Derate above $25^\circ\text{C}$		0.41
Junction Temperature	$T_J$	+150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~+150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Drain current limited by maximum junction temperature
3. Repetitive Rating: Pulse width limited by maximum junction temperature
4.  $L = 5.5\text{mH}$ ,  $I_{AS} = 16\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
5.  $I_{SD} \leq 16\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	$\theta_{JC}$	2.4	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ( $T_c=25^\circ\text{C}$ , unless otherwise specified)

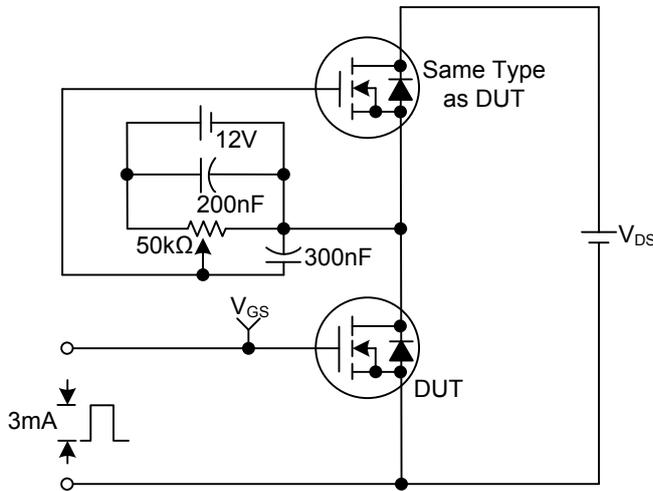
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	500			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=500\text{V}$ , $V_{GS}=0\text{V}$			1	$\mu\text{A}$
Gate- Source Leakage Current	Forward	$I_{GSS}$			+100	nA
	Reverse				-100	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$ , $I_D=8\text{A}$		0.31	0.38	$\Omega$
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0\text{V}$ , $V_{DS}=25\text{V}$ , $f=1.0\text{MHz}$		1495	1945	pF
Output Capacitance	$C_{OSS}$			235	310	pF
Reverse Transfer Capacitance	$C_{RSS}$			20	30	pF
<b>SWITCHING PARAMETERS</b>						
Total Gate Charge	$Q_G$	$V_{GS}=10\text{V}$ , $V_{DS}=400\text{V}$ , $I_D=16\text{A}$ (Note 6, 7)		32	45	nC
Gate to Source Charge	$Q_{GS}$			8.5		nC
Gate to Drain Charge	$Q_{GD}$			14		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=250\text{V}$ , $I_D=16\text{A}$ , $R_G=25\Omega$ (Note 6, 7)		40	90	ns
Rise Time	$t_R$			150	310	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			65	140	ns
Fall-Time	$t_F$			80	170	ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	$I_S$				9.2	A
Maximum Body-Diode Pulsed Current	$I_{SM}$				37	A
Drain-Source Diode Forward Voltage	$V_{SD}$	$I_S=16\text{A}$ , $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time	$t_{RR}$	$I_S=16\text{A}$ , $V_{GS}=0\text{V}$ , $di_F/dt=100\text{A}/\mu\text{s}$ (Note 6)		490		ns
Body Diode Reverse Recovery Charge	$Q_{RR}$				5.0	

Notes: 6. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$

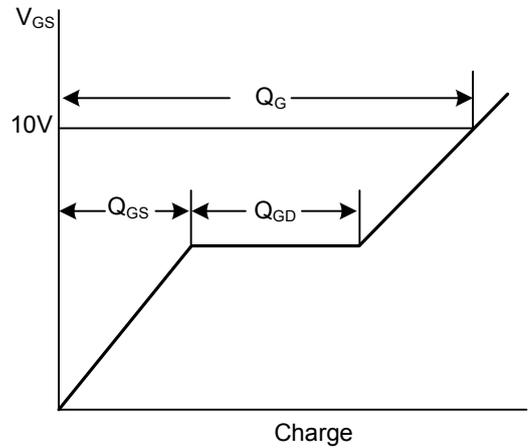
7. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

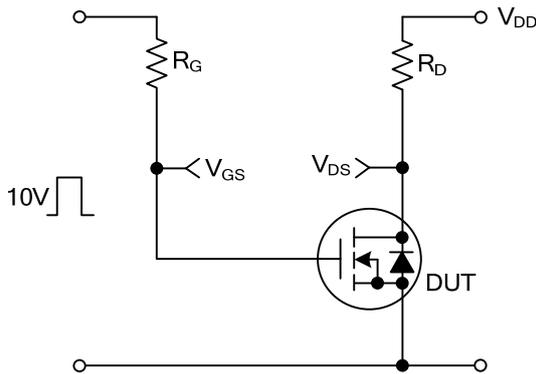
Gate Charge Test Circuit



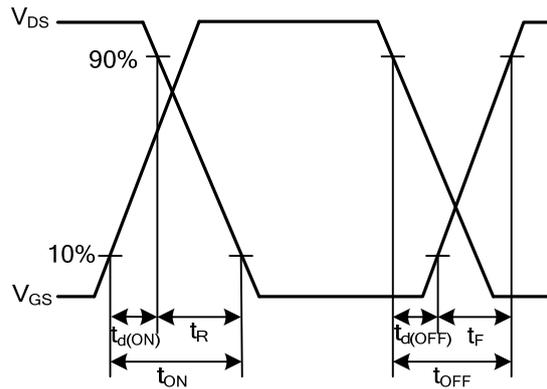
Gate Charge Waveforms



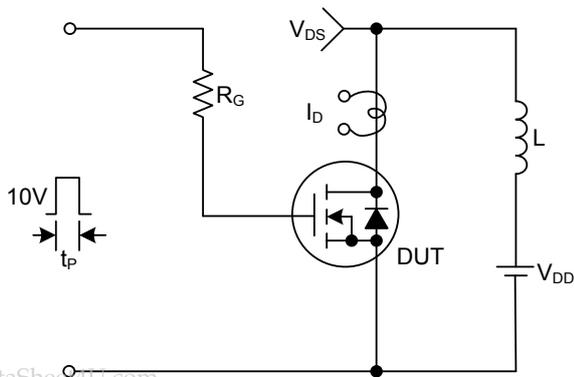
Resistive Switching Test Circuit



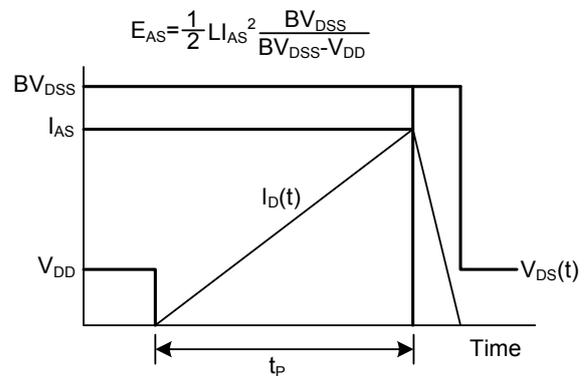
Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



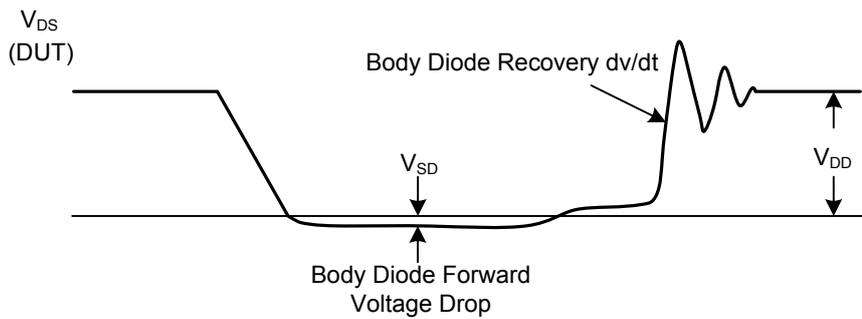
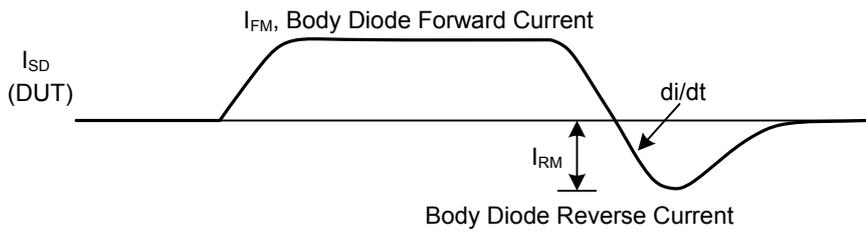
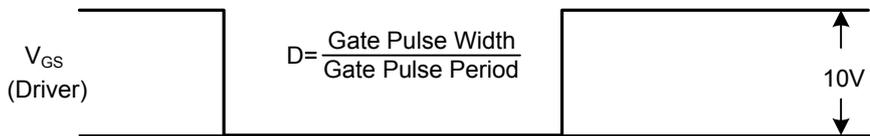
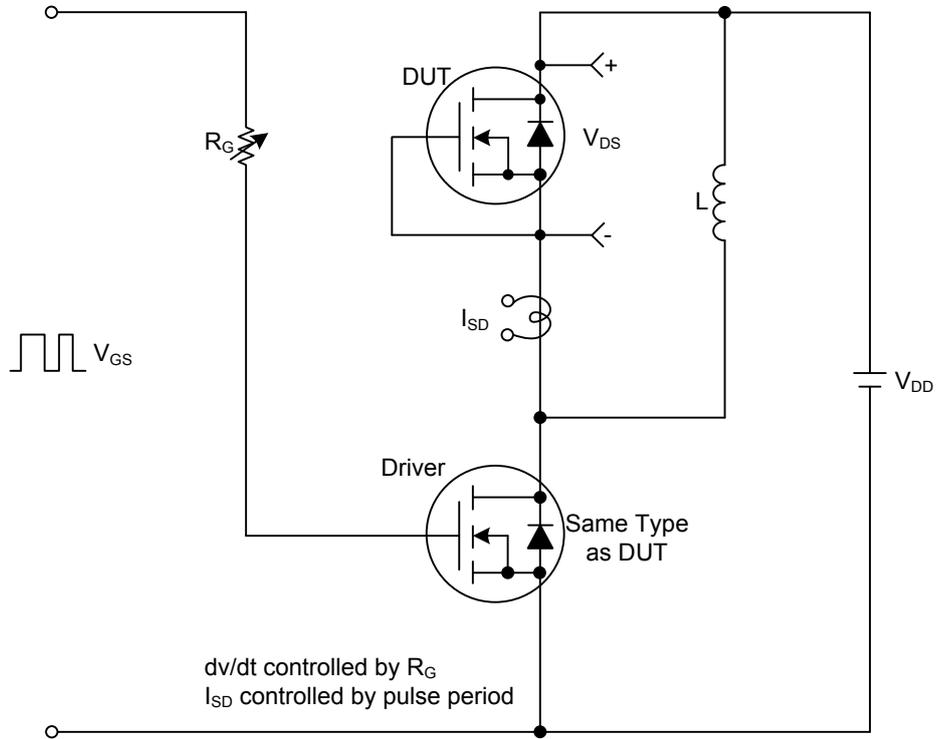
Unclamped Inductive Switching Waveforms



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■ TEST CIRCUITS AND WAVEFORMS(Cont.)

Peak Diode Recovery dv/dt Test Circuit & Waveforms



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